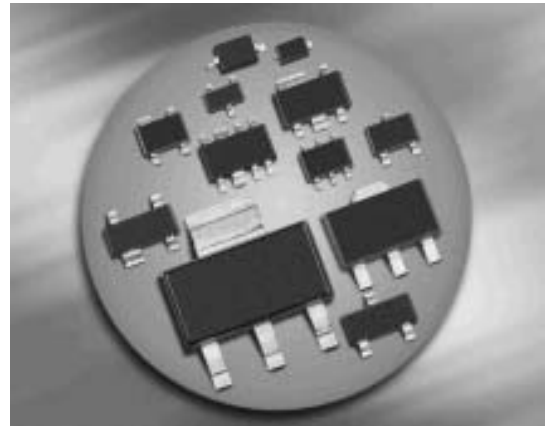


**Silicon Variable Capacitance Diode**

- For tuning of extended frequency band in VHF TV / VTR tuners
- High capacitance ratio
- Low series inductance
- Low series resistance
- Excellent uniformity and matching due to "in-line" matching assembly procedure
- Pb-free (RoHS compliant) package <sup>1)</sup>
- Qualified according AEC Q101



**BB639C**  
**BB659C/-02V**



Type	Package	Configuration	$L_S$ (nH)	Marking
BB639C	SOD323	single	1.8	yellow S
BB659C	SCD80	single	0.6	HH
BB659C-02V	SC79	single	0.6	H

**Maximum Ratings** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	$V_R$	30	V
Peak reverse voltage ( $R \geq 5\text{k}\Omega$ )	$V_{RM}$	35	
Forward current	$I_F$	20	mA
Operating temperature range	$T_{op}$	-55 ... 150	°C
Storage temperature	$T_{stg}$	-55 ... 150	

<sup>1</sup>Pb-containing package may be available upon special request

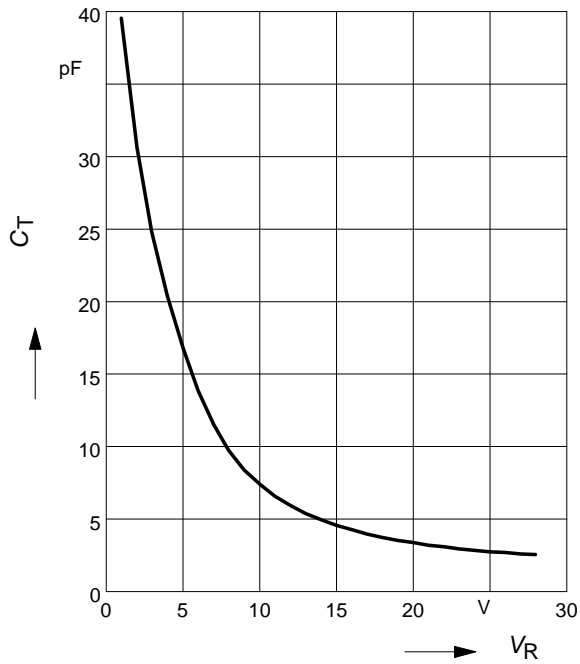
**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Reverse current	$I_R$				nA
$V_R = 30\text{ V}$		-	-	10	
$V_R = 30\text{ V}, T_A = 85^\circ\text{C}$		-	-	200	
<b>AC Characteristics</b>					
Diode capacitance	$C_T$				pF
$V_R = 1\text{ V}, f = 1\text{ MHz}$		36.5	39	42	
$V_R = 2\text{ V}, f = 1\text{ MHz}$		27	30.2	33.2	
$V_R = 25\text{ V}, f = 1\text{ MHz}$		2.5	2.72	3.05	
$V_R = 28\text{ V}, f = 1\text{ MHz}$		2.4	2.55	2.75	
Capacitance ratio	$C_{T1}/C_{T28}$	14.2	15.3	-	
$V_R = 1\text{ V}, V_R = 28\text{ V}, f = 1\text{ MHz}$					
Capacitance ratio	$C_{T2}/C_{T25}$	9.5	11.1	-	
$V_R = 2\text{ V}, V_R = 25\text{ V}, f = 1\text{ MHz}$					
Capacitance matching <sup>1)</sup>	$\Delta C_T/C_T$				%
$V_R = 1\text{V to } 28\text{V}, f = 1\text{ MHz}, 7\text{ diodes sequence, BB639C}$		-	-	2.5	
$V_R = 1\text{V to } 28\text{V}, f = 1\text{ MHz}, 4\text{ diodes sequence, BB659C/-02V}$		-	0.3	1	
$V_R = 1\text{V to } 28\text{V}, f = 1\text{ MHz}, 7\text{ diodes sequence, BB659C/-02V}$		-	0.5	2	
Series resistance	$r_S$	-	0.6	0.7	$\Omega$
$V_R = 5\text{ V}, f = 470\text{ MHz}$					

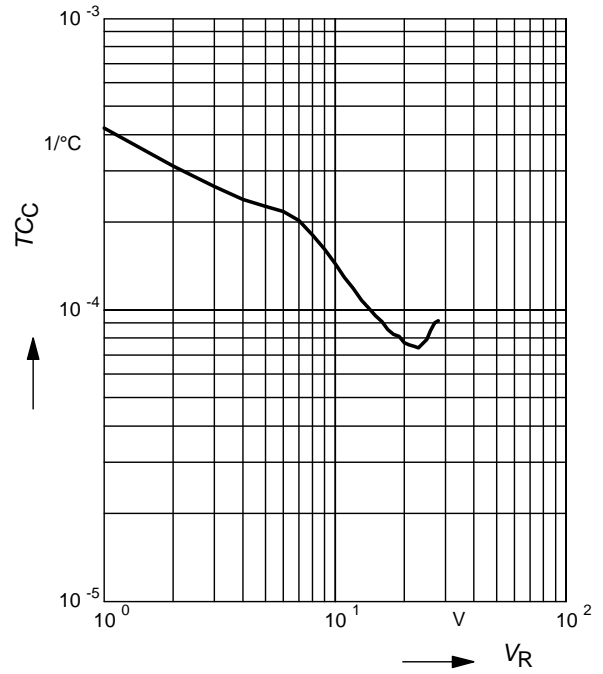
<sup>1</sup>For details please refer to Application Note 047

**Diode capacitance  $C_T = f(V_R)$**

$f = 1\text{MHz}$

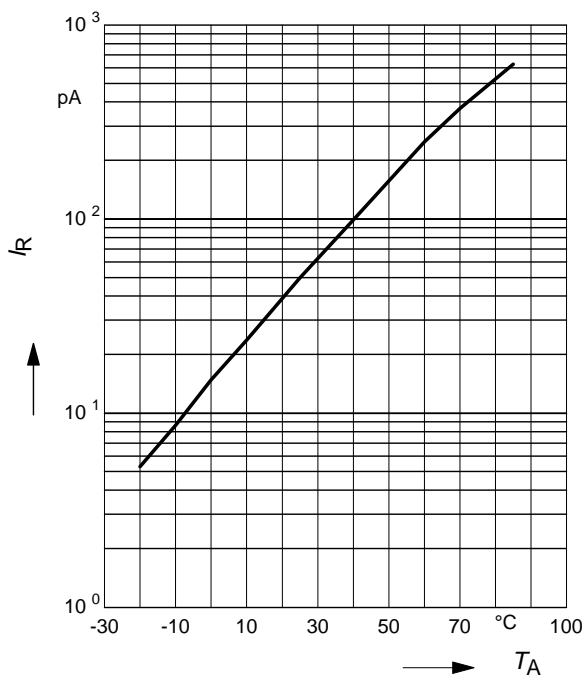


**Temperature coefficient of the diode capacitance  $T_{CC} = f(V_R)$**



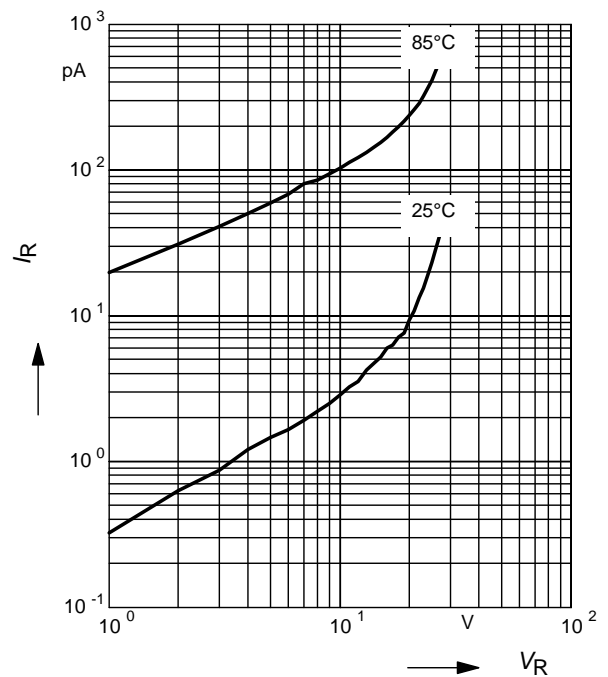
**Reverse current  $I_R = f(T_A)$**

$V_R = 28\text{V}$

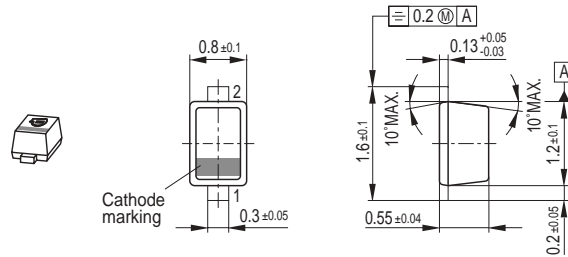


**Reverse current  $I_R = f(V_R)$**

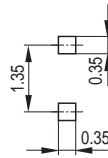
$T_A = \text{Parameter}$



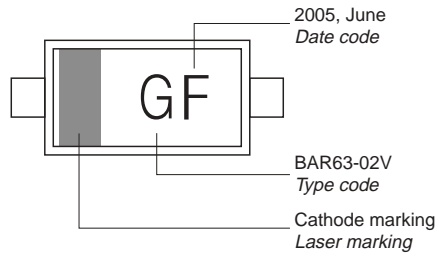
Package Outline



Foot Print

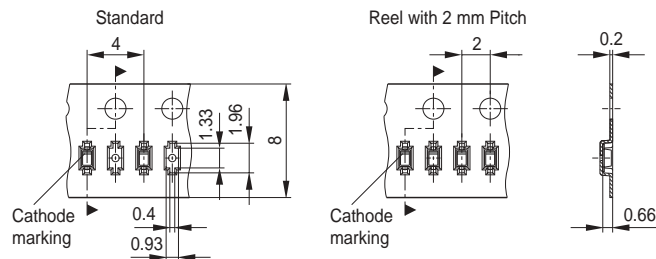


Marking Layout (Example)

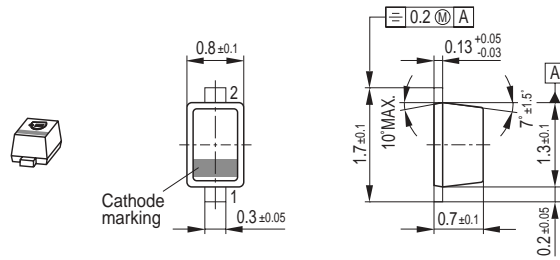


Standard Packing

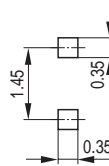
Reel  $\varnothing$ 180 mm = 3.000 Pieces/Reel  
 Reel  $\varnothing$ 180 mm = 8.000 Pieces/Reel (2 mm Pitch)  
 Reel  $\varnothing$ 330 mm = 10.000 Pieces/Reel



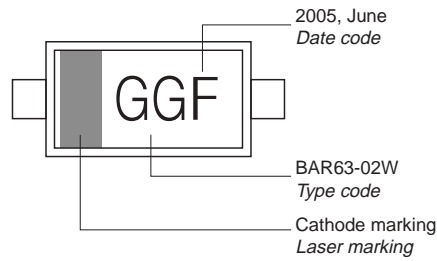
Package Outline



Foot Print

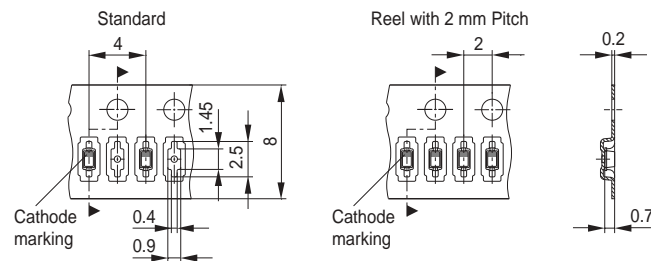


Marking Layout (Example)



Standard Packing

Reel  $\varnothing$ 180 mm = 3.000 Pieces/Reel  
 Reel  $\varnothing$ 180 mm = 8.000 Pieces/Reel (2 mm Pitch)  
 Reel  $\varnothing$ 330 mm = 10.000 Pieces/Reel

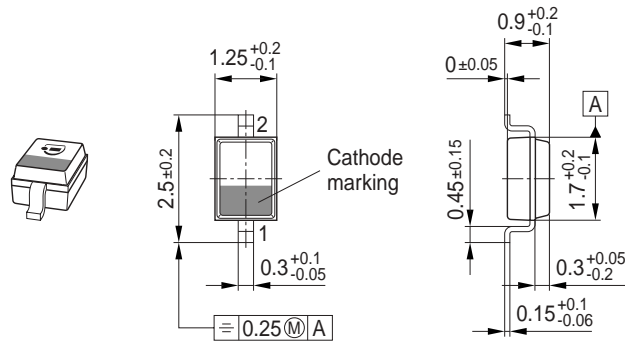


Date Code marking for discrete packages with  
one digit (SCD80, SC79, SC75<sup>1)</sup>) CES-Code

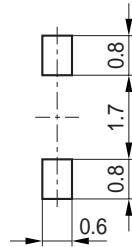
Month	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014
01	a	p	A	P	a	p	A	P	a	p	A	P
02	b	q	B	Q	b	q	B	Q	b	q	B	Q
03	c	r	C	R	c	r	C	R	c	r	C	R
04	d	s	D	S	d	s	D	S	d	s	D	S
05	e	t	E	T	e	t	E	T	e	t	E	T
06	f	u	F	U	f	u	F	U	f	u	F	U
07	g	v	G	V	g	v	G	V	g	v	G	V
08	h	x	H	X	h	x	H	X	h	x	H	X
09	j	y	J	Y	j	y	J	Y	j	y	J	Y
10	k	z	K	Z	k	z	K	Z	k	z	K	Z
11	l	2	L	4	l	2	L	4	l	2	L	4
12	n	3	N	5	n	3	N	5	n	3	N	5

1) New Marking Layout for SC75, implemented at October 2005.

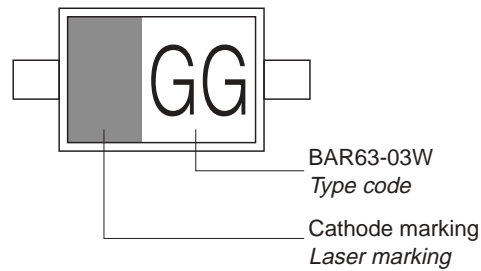
Package Outline



Foot Print

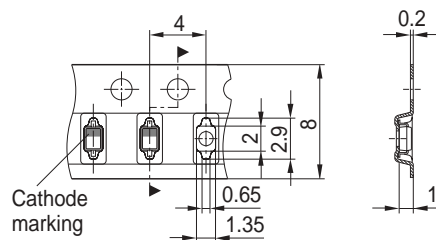


Marking Layout (Example)



Standard Packing

Reel  $\varnothing$ 180 mm = 3.000 Pieces/Reel  
 Reel  $\varnothing$ 330 mm = 10.000 Pieces/Reel



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